

GJ1182

PNP SILICON EPITAXIAL PLANAR TRANSISTOR

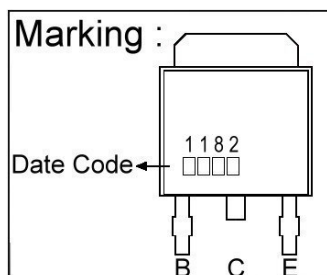
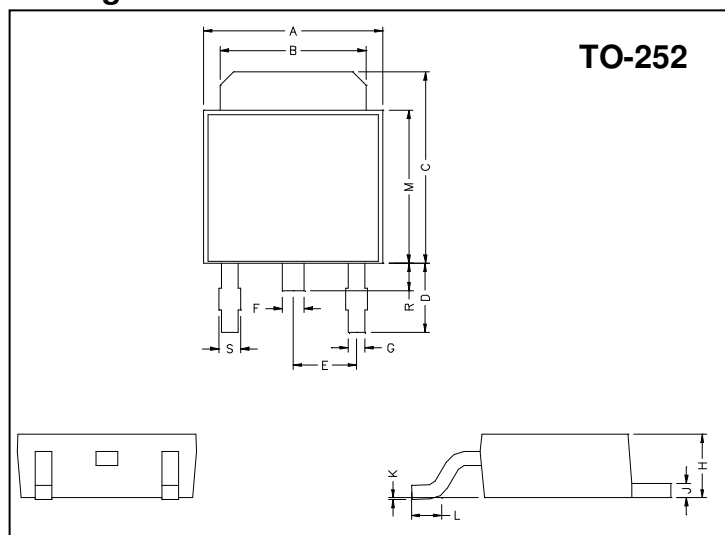
Description

The GJ1182 is designed for medium power amplifier applications.

Features

- Low collector saturation voltage : $V_{CE(sat)} = -0.5V$ (Typ.)

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.40	6.80	G	0.50	0.70
B	5.20	5.50	H	2.20	2.40
C	6.80	7.20	J	0.45	0.55
D	2.40	3.00	K	0	0.15
E	2.30 REF.		L	0.90	1.50
F	0.70	0.90	M	5.40	5.80
S	0.60	0.90	R	0.80	1.20

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Ratings	Unit
Junction Temperature	T_j	+150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~+150	$^\circ\text{C}$
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-2	A
Collector Current (Pulse, $P_w=100\text{ms}$)	I_C	-3	A
Total Power Dissipation($T_c=25^\circ\text{C}$)	P_D	10	W

Electrical Characteristics ($T_a = 25^\circ\text{C}$, unless otherwise noted)

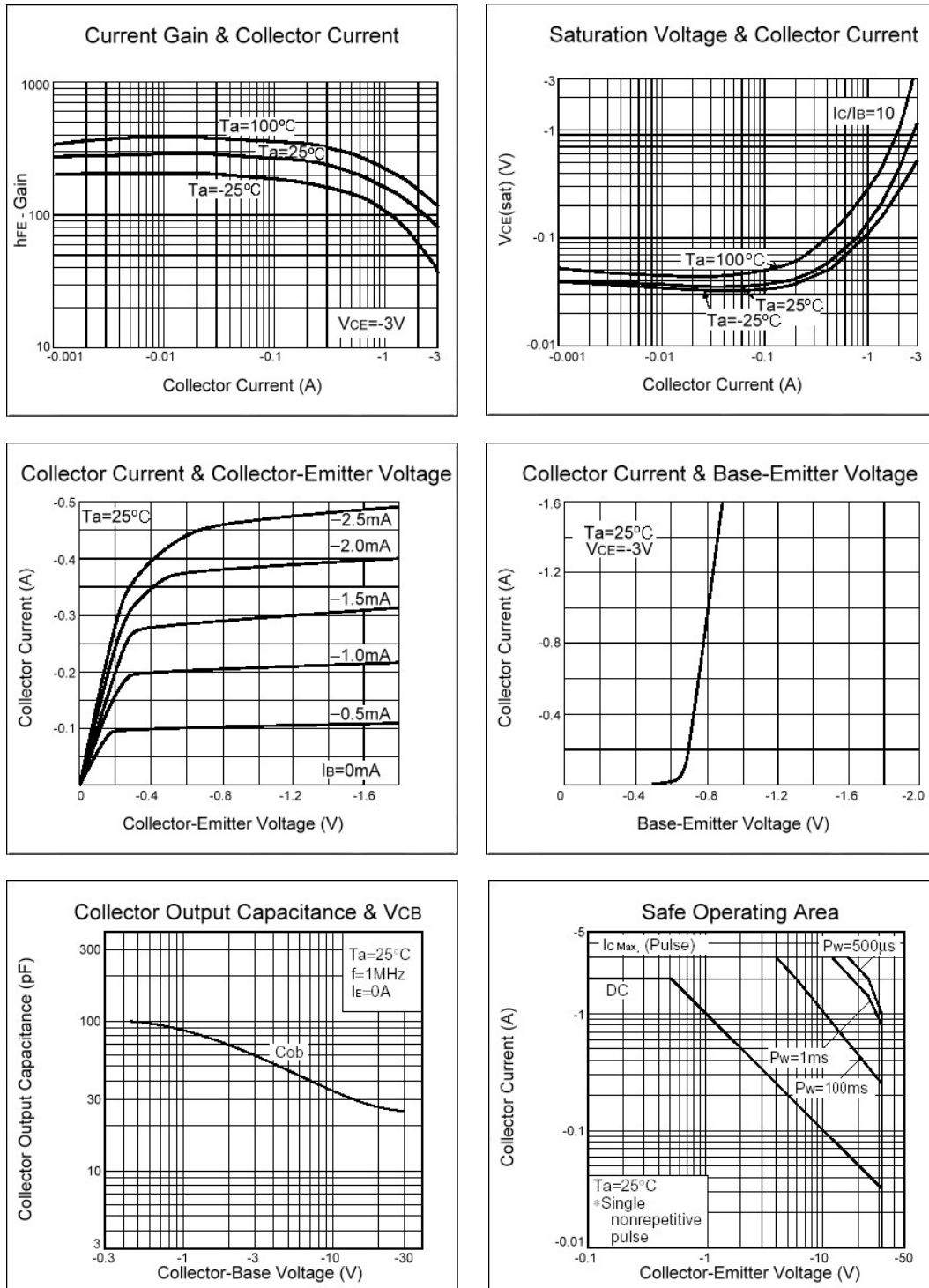
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
V_{CBO}	-40	-	-	V	$I_C = -50\mu\text{A}$, $I_E = 0$
V_{CEO}	-32	-	-	V	$I_C = -1\text{mA}$, $I_B = 0$
V_{EBO}	-5	-	-	V	$I_E = -50\mu\text{A}$, $I_C = 0$
I_{CBO}	-	-	-1	μA	$V_{CB} = -20\text{V}$, $I_E = 0$
I_{EBO}	-	-	-1	μA	$V_{EB} = -4\text{V}$, $I_C = 0$
$*V_{CE(sat)}$	-	-500	-800	mV	$I_C = -2\text{A}$, $I_B = -200\text{mA}$
$*h_{FE}$	82	-	390		$V_{CE} = -3\text{V}$, $I_C = -500\text{mA}$
f_T	-	100	-	MHz	$V_{CE} = -5\text{V}$, $I_C = -500\text{mA}$, $f = 100\text{MHz}$
C_{ob}	-	50	-	pF	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$

* Pulse Test: Pulse Width $\leq 380\mu\text{s}$, Duty Cycle $\leq 2\%$

Classification Of h_{FE}

Rank	P	Q	R
Range	82 ~ 180	120 ~ 270	180 ~ 390

Characteristics Curve



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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
- TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
- TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165